

L Number	Hits	Search Text	DB	Time stamp
1	30	self adj aligned adj storage adj node	USPAT	2004/08/23 09:08
2	0	(self adj aligned adj storage adj node) and (recessed adj portion) and recess	USPAT	2004/08/23 09:09
3	3	(self adj aligned adj storage adj node) and recess and surface	USPAT	2004/08/23 09:11
4	3	((self adj aligned adj storage adj node) and recess and surface) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive or recess or recessed or potion)	USPAT	2004/08/23 09:26
5	1	("6432795").PN.	USPAT	2004/08/23 09:26
6	1	((("6432795").PN.) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive or recess or recessed or potion)	USPAT	2004/08/23 09:39
7	1	("6268246").PN.	USPAT	2004/08/23 09:39
8	1	((("6268246").PN.) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive or recess or recessed or potion)	USPAT	2004/08/23 09:51
9	1	("6002149").PN.	USPAT	2004/08/23 09:51
10	1	((("6002149").PN.) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive or recess or recessed or potion)	USPAT	2004/08/23 10:07
11	3	(recessed adj portion) and (surface adj3 storage adj node adj contact)	USPAT	2004/08/23 10:02
12	3	((recessed adj portion) and (surface adj3 storage adj node adj contact)) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive or recess or recessed or potion)	USPAT	2004/08/23 10:20
13	1	("6236079").PN.	USPAT	2004/08/23 10:21
14	1	("6002149").PN.	USPAT	2004/08/23 10:21
15	1	("6268246").PN.	USPAT	2004/08/23 10:22
16	1713	(438/253).CCLS.	USPAT	2004/08/23 10:22
17	516	(438/254).CCLS.	USPAT	2004/08/23 10:22
18	556	(438/255).CCLS.	USPAT	2004/08/23 10:22
19	1715	(438/396).CCLS.	USPAT	2004/08/23 10:22
20	468	(438/397).CCLS.	USPAT	2004/08/23 10:22
21	621	(438/398).CCLS.	USPAT	2004/08/23 10:23
22	277	(438/439).CCLS.	USPAT	2004/08/23 10:23
23	178	(438/443).CCLS.	USPAT	2004/08/23 10:23
24	580	(438/680).CCLS.	USPAT	2004/08/23 10:23
25	331	(438/689).CCLS.	USPAT	2004/08/23 10:23
26	769	(438/706).CCLS.	USPAT	2004/08/23 10:23
27	777	(438/745).CCLS.	USPAT	2004/08/23 10:23
-	0	semiconductor adj device adj2 self adj aligned adj storage adj node	USPAT	2004/08/19 17:50

-	118	(self adj aligned adj storage adj node) and first and second insulating and interlayer and conductive and contact and etch and etching and stop and stack and structure and mask and high and density and plasma and oxide	USPAT	2004/08/19 17:53
-	1	(self adj aligned adj storage adj node) and first and second and insulating and interlayer and conductive and contact and etch and etching and stop and stack and structure and mask and high and density and plasma and oxide	USPAT	2004/08/19 17:56
-	1		USPAT	2004/08/19 17:54
-	1		USPAT	2004/08/19 17:54
-	1		USPAT	2004/08/19 17:55
-	1		USPAT	2004/08/19 17:55
-	1		USPAT	2004/08/19 17:56
-	1	((self adj aligned adj storage adj node) and first and second and insulating and interlayer and conductive and contact and etch and etching and stop and stack and structure and mask and high and density and plasma and oxide) and (etching or mask or storage or node or device or semiconductor or recess or hole or portion or recessed or bottom or upper or protrudes or contact or removing or interlayer or edge or surfae or demension or etch or back or thicknes or material or conductive)	USPAT	2004/08/23 09:11

8/23/04